## Supporting Information for

## Nonvolatile Electro-Mechanical Coupling in Two-Dimensional Lattices

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Fig. S1 Crystal structure of SL ReIrGe ${ }_{2} \mathrm{~S}_{6}$ from top and side views.


Fig. S2 Variation of total energy during AIMD ( $300 \mathrm{~K}, 3 \mathrm{ps}$ ) simulations. Inset is crystal structure of $\mathrm{SL}^{\operatorname{ReIrGe}} \mathrm{C}_{2} \mathrm{~S}_{6}$ taken from the end of AIMD.
(a)

(b)

(c)




(d)

(e)

(f)




Fig. S3 Structure generation during CI-NEB for bilayer $\mathrm{MoS}_{2} / \operatorname{ReIrGe}_{2} \mathrm{~S}_{6}$. Yellow, blue, gray, brown, and purple spheres represent $\mathrm{S}, \mathrm{Ge}, \mathrm{Re}, \mathrm{Ir}$, and Mo atoms, respectively.


Fig. S4 (a-b) Band structures of $\mathrm{MoS}_{2} / \operatorname{ReIrGe}_{2} \mathrm{~S}_{6}$ bilayer with $\mathrm{P} \uparrow$ and $\mathrm{P} \downarrow$.


Fig. S5 (a-b) Band structures with SOC of $\mathrm{MoS}_{2} / \operatorname{ReIrGe}_{2} \mathrm{~S}_{6}$ bilayer with $\mathrm{P} \uparrow$ and $\mathrm{P} \downarrow$.




Fig. S6 The charge density difference of $\mathrm{Sb} / \mathrm{In}_{2} \mathrm{Se}_{3}$ bilayer under $\mathrm{P} \uparrow$ and $\mathrm{P} \downarrow$. The isosurface value is set to 0.02 electrons per $\AA^{3}$.
(a)

(b)



(d)


(e)







Fig. S7 Structure generation during CI-NEB for bilayer $\mathrm{Sb} / \mathrm{In}_{2} \mathrm{Se}_{3}$. Brown, green, and purple spheres represent $\mathrm{Sb}, \mathrm{Se}$, and In atoms, respectively.


Fig. S8 Minimum energy pathway of FE switching as a function of step number within NEB for $\mathrm{Sb} / \mathrm{In}_{2} \mathrm{Se}_{3}$ bilayer.
(a)

(b)




Fig. S9 (a-b) Crystal structures of $\mathrm{PdTe}_{2} / \mathrm{In}_{2} \mathrm{Se}_{3}$ bilayer under $\mathrm{P} \uparrow$ and $\mathrm{P} \downarrow$ configurations. Orange, blue, yellow and brown spheres represent $\mathrm{Te}, \mathrm{Pd}, \mathrm{Se}$ and In atoms, respectively. (c-d) Band structures of $\mathrm{PdTe}_{2} / \mathrm{In}_{2} \mathrm{Se}_{3}$ bilayer under $\mathrm{P} \uparrow$ and $\mathrm{P} \downarrow$ configurations.
(a)











(b)











(c)







$a \sigma^{a} \sigma^{a} 0$
$0 \sigma^{2} \sigma^{2}$

$$
\begin{aligned}
& \sigma^{2} \sigma^{2} 0 \\
& 00
\end{aligned}
$$



(d)






$\sigma_{0}^{0} 0_{0}^{\infty} 0$
$a \sigma^{a} \sigma^{a}=$
$a_{0}^{a} \sigma^{2}$
$\sum_{0}^{a} \sigma^{2} 0_{0}^{0} 0$



Fig. S10 Structure generation and Minimum energy pathway of FE switching for bilayer $\operatorname{In}_{2} \operatorname{Se}_{3}$. (a) From $\mathrm{P} \uparrow \uparrow$ to $\mathrm{P} \uparrow \downarrow$. (b) From $\mathrm{P} \uparrow \uparrow$ to $\mathrm{P} \downarrow \uparrow$. (c) From $\mathrm{P} \uparrow \uparrow$ to $\mathrm{P} \downarrow \downarrow$. (d) From $\mathrm{P} \downarrow \uparrow$ to $\mathrm{P} \uparrow \downarrow$. Green, and purple spheres represent $\mathrm{Sb}, \mathrm{Se}$, and In atoms, respectively.


Fig. S11 Plane-averaged potential of bilayer $\mathrm{In}_{2} \mathrm{Se}_{3}$ along z direction under (a) $\mathrm{P} \uparrow \uparrow$, (b) $\mathrm{P} \uparrow \downarrow$ and (c) $\mathrm{P} \downarrow \uparrow$ configurations.

